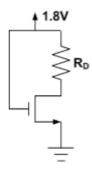
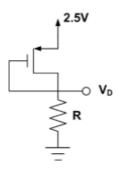
EE 315 Module 4 Practice Problems

- 1. An NMOS transistor is characterized as follows: V_{DS} =0.1V, V_t =1.5V, k'_n = 25 μ A/V², and W/L = 10. Find the drain current for V_{GS} =0V, 1V, 2V, and 3V.
- 2. An NMOS transistor is characterized as follows: $V_{DS}=3.3V$, $V_t=1.V$, $k'_n=37.5 \,\mu\text{A/V}^2$, and W/L = 10. Find the drain current for $V_{GS}=0V$, 1V, 2V, and 3V.
- 3. Identify the region of operation and the drain current for an NMOS transistor where the $k'_n=25~\mu\text{A/V2}$, $V_t=1\text{V}$ and W/L=10.
 - a. V_{GS} =5V and V_{DS} =6V
 - b. $V_{GS}=0V$ and $V_{DS}=6V$
 - c. $V_{GS}=2V$ and $V_{DS}=-0.5V$
- 4. An NMOS transistor has V_t =0.8V, k'^n = 0.05 mA/ V^2 , and W/L = 2. The device is biased at V^{GS} =2.5 V. Calculate the drain current and the resistance r_0 for V_{DS} =2V and 10V for
 - a. λ=0
 - b. $\lambda = 0.02$
 - c. V_A=35V
- 5. A PMOS transistor has $k'_p = 0.1 \text{ mA/V}^2$, W/L = 2, $V_t = -2V$ and $V_{SG} = 3V$. Find the region of operation and the drain current for:
 - a. $V_{SD}=0.5V$
 - b. $V_{SD}=2V$
 - c. $V_{SD}=5V$
- 6. Consider the following NMOS circuit where V_t =0.5V, k'_n = 0.4 mA/V2, and W/L = 5. If the circuit operates at the edge of saturation with a drain current of 1mA, find the resistor, R_D .



7. Consider the following PMOS circuit where V_t =-0.6V, k'_p = 250 μ A/V², and L = 0.25 μ m. find the values required for W and R such that the drain current is 0.8mA and the drain voltage is 1.5V.



8. Find the labeled voltages and currents in the following circuit where V_{tn} =+1V, V_{tp} = -1V, k'_{n} = 20 μ A/V², k'_{p} = 8 μ A/V² and W/L = 3 (for both n and p-type transistors).

